

N-channel 500 V, 0.40 Ω typ., 8.5 A MDmesh™ II Power MOSFET in a DPAK package

Datasheet - production data

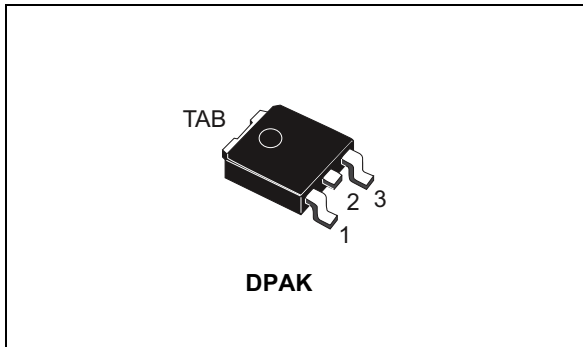
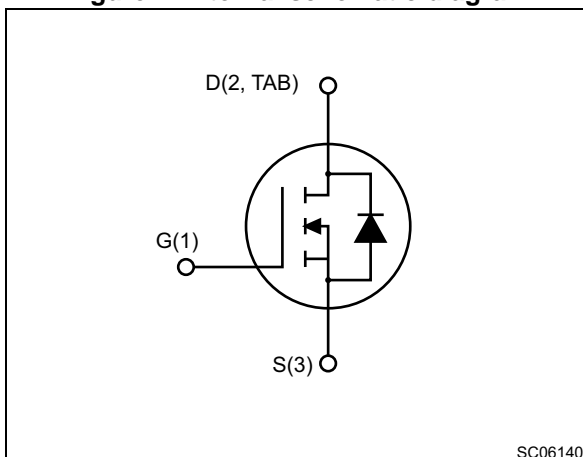


Figure 1. Internal schematic diagram



Features

Order code	$V_{DS} @ T_J \text{ max}$	$R_{DS(on)} \text{ max}$	I_D
STD11NM50N	550 V	0.47 Ω	8.5 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order code	Marking	Package	Packaging
STD11NM50N	11NM50N	DPAK	Tape and reel

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	500	V
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	8.5	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6	A
$I_{DM}^{(1)}$	Drain current (pulsed)	34	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area .
2. $I_{SD} \leq 8.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DSpeak} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.79	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max ⁽¹⁾	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_{jmax})	3	A
E_{AS}	Single pulse avalanche energy (starting $T_J=25\text{ }^\circ\text{C}$, $I_D=I_{AR}$, $V_{DD}=50\text{ V}$)	150	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	500			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 500 V V _{DS} = 500 V, T _C = 125 °C			1 100	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 25 V			±100	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 4.5 A		0.40	0.47	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0	-	547	-	pF
C _{oss}	Output capacitance		-	42	-	pF
C _{rss}	Reverse transfer capacitance		-	2	-	pF
C _{oss eq. (1)}	Equivalent output capacitance	V _{GS} = 0, V _{DS} = 0 to 400 V	-	210	-	pF
Q _g	Total gate charge	V _{DD} = 400 V, I _D = 8.5 A, V _{GS} = 10 V (see Figure 14)	-	19	-	nC
Q _{gs}	Gate-source charge		-	3.7	-	nC
Q _{gd}	Gate-drain charge		-	10	-	nC
R _G	Gate input resistance	f=1 MHz, I _D =0	-	5.8	-	Ω

1. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 7. Switching times

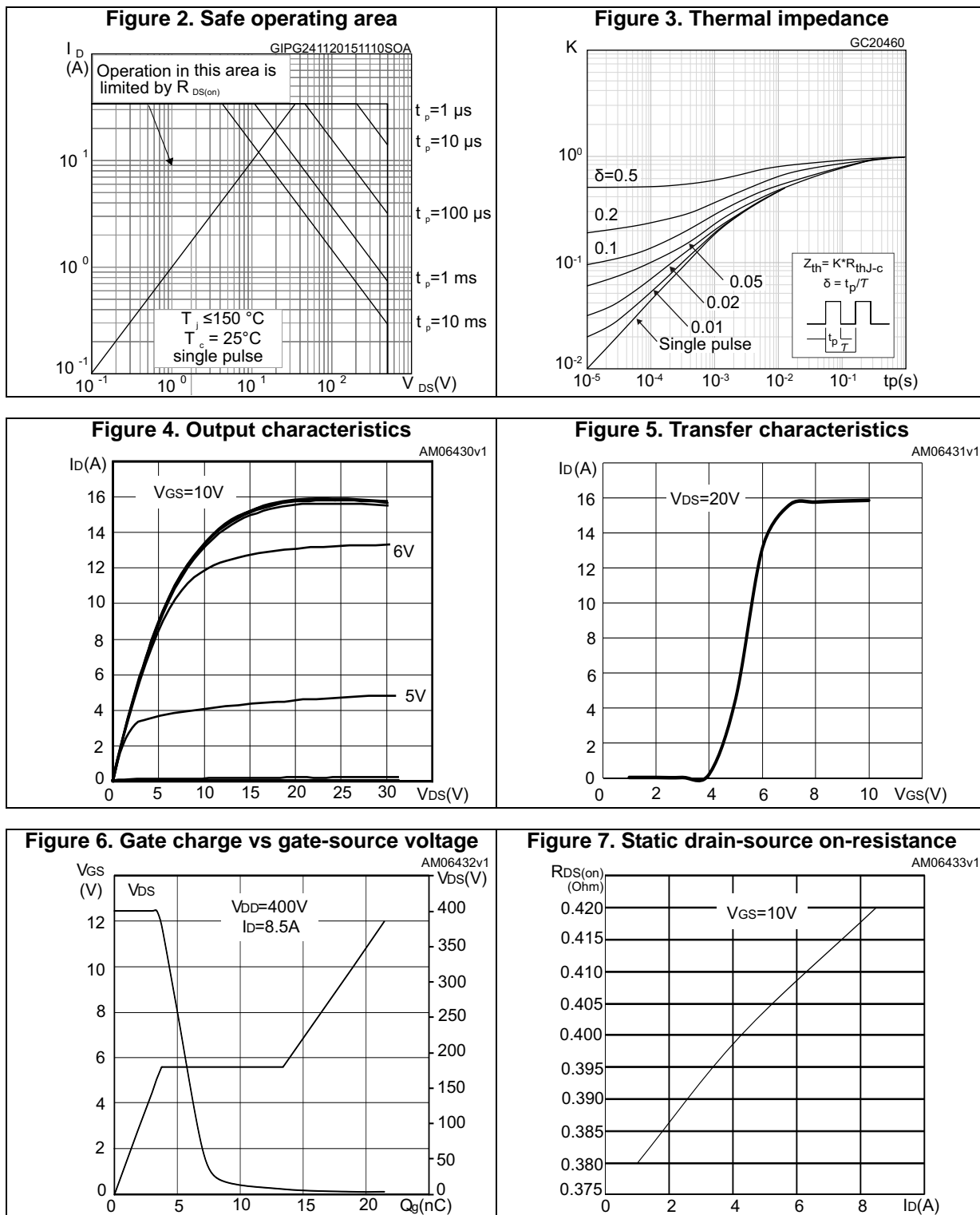
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250\text{ V}$, $I_D = 4.25\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15 and Figure 18)	-	8	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	33	-	ns
t_f	Fall time		-	10	-	ns

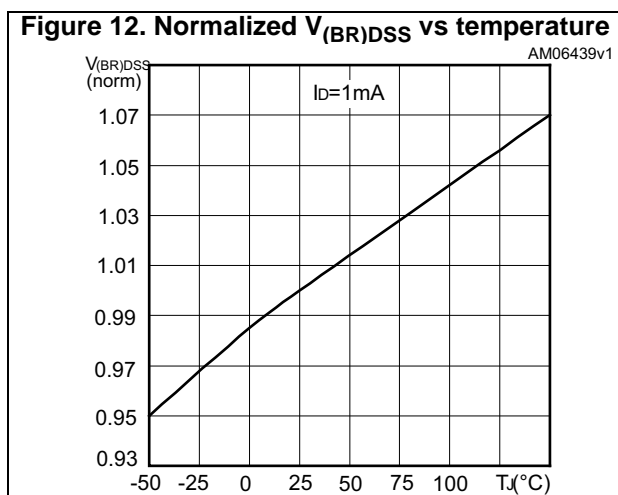
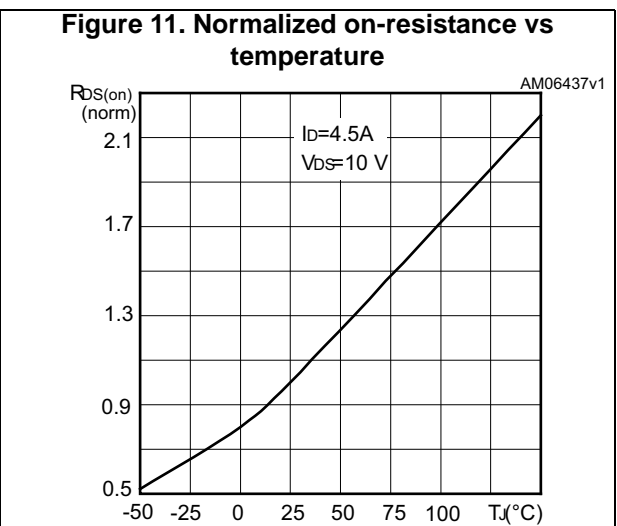
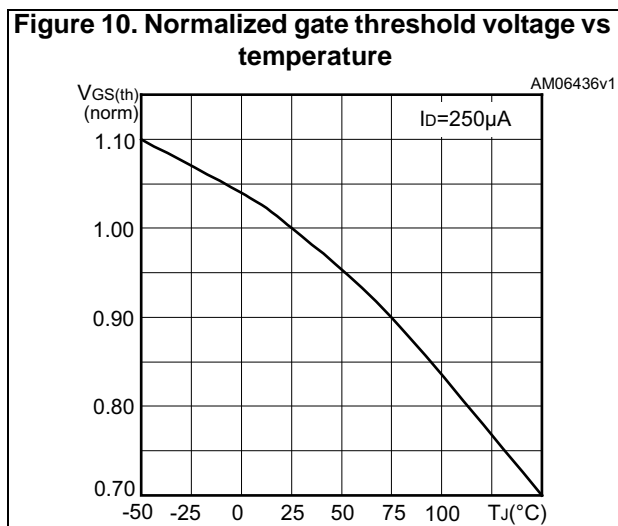
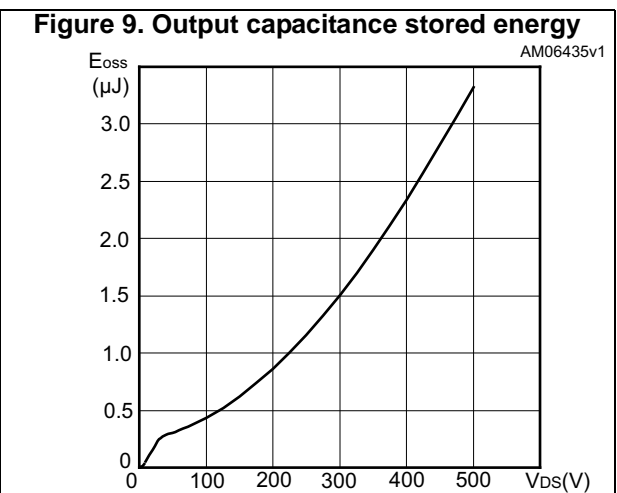
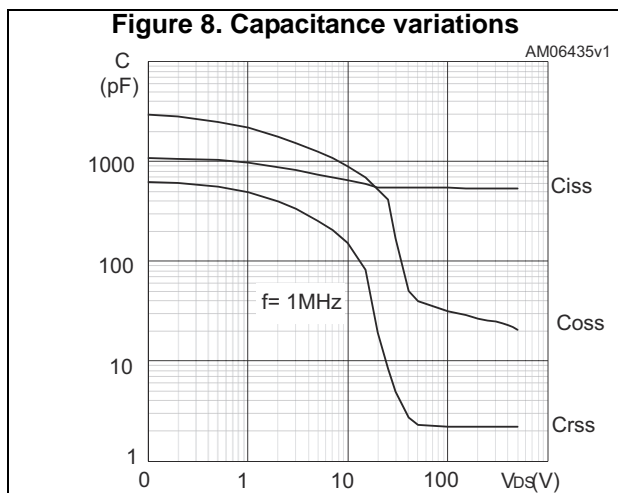
Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		8.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				34	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 8.5\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 8.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	230		ns
Q_{rr}	Reverse recovery charge		-	2.1		μC
I_{RRM}	Reverse recovery current	$V_{DD} = 60\text{ V}$ (see Figure 15)	-	18		A
t_{rr}	Reverse recovery time	$I_{SD} = 8.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	275		ns
Q_{rr}	Reverse recovery charge		-	2.5		μC
I_{RRM}	Reverse recovery current	$V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15)	-	18		A

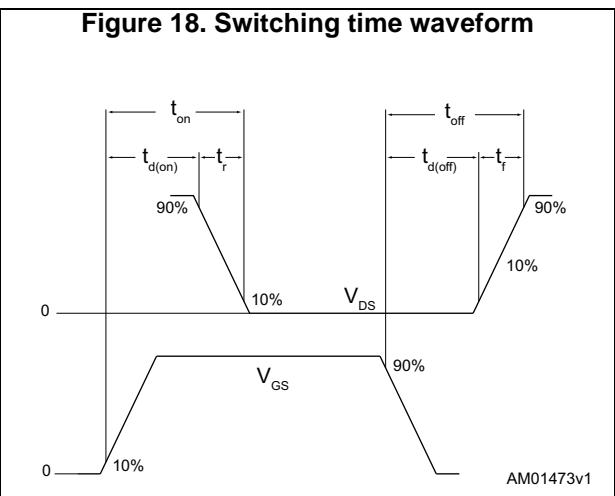
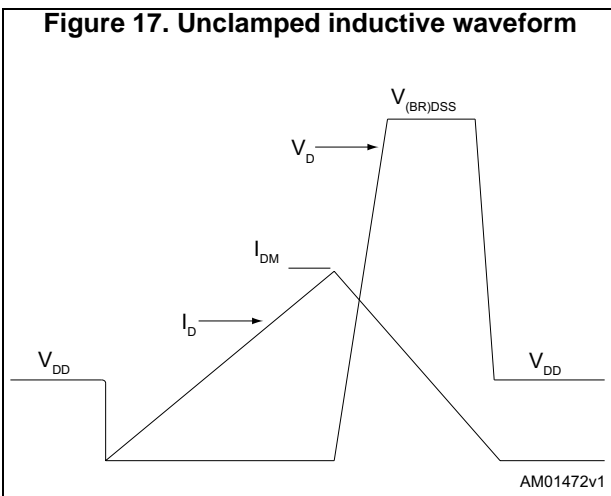
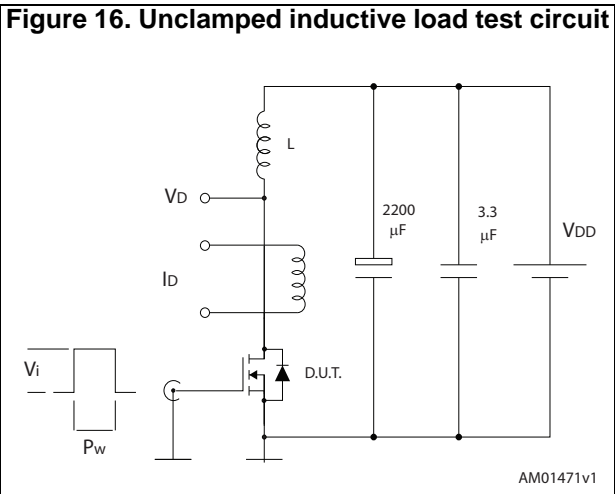
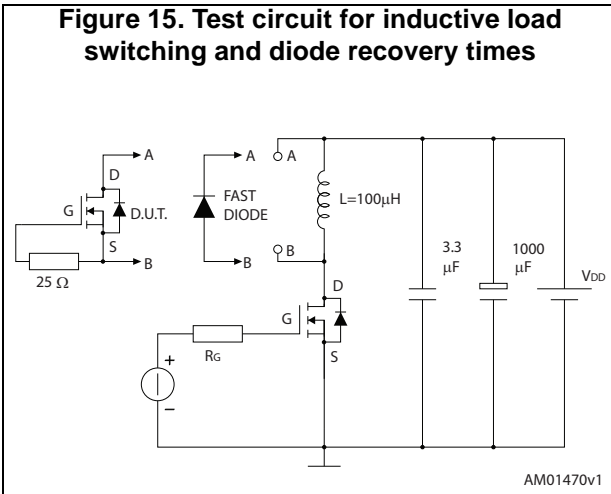
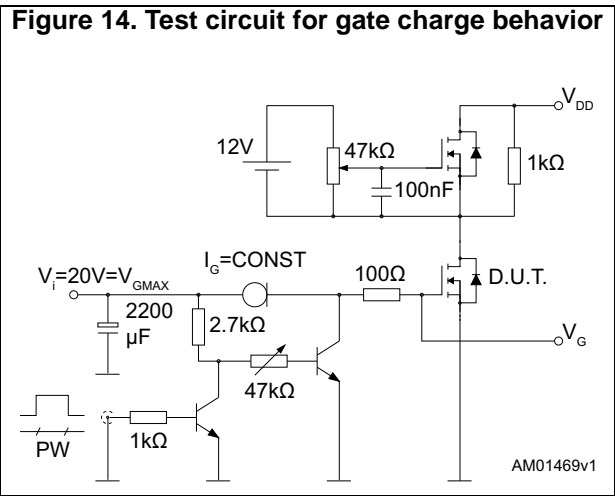
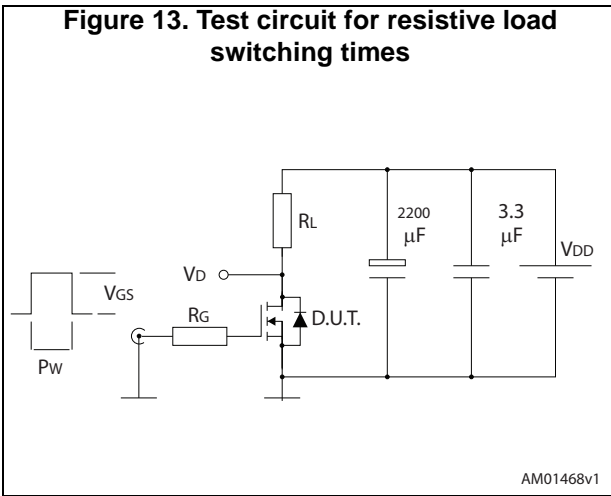
1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)





3 Test circuits



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK type A package information

Figure 19. DPAK (TO-252) type A package outline

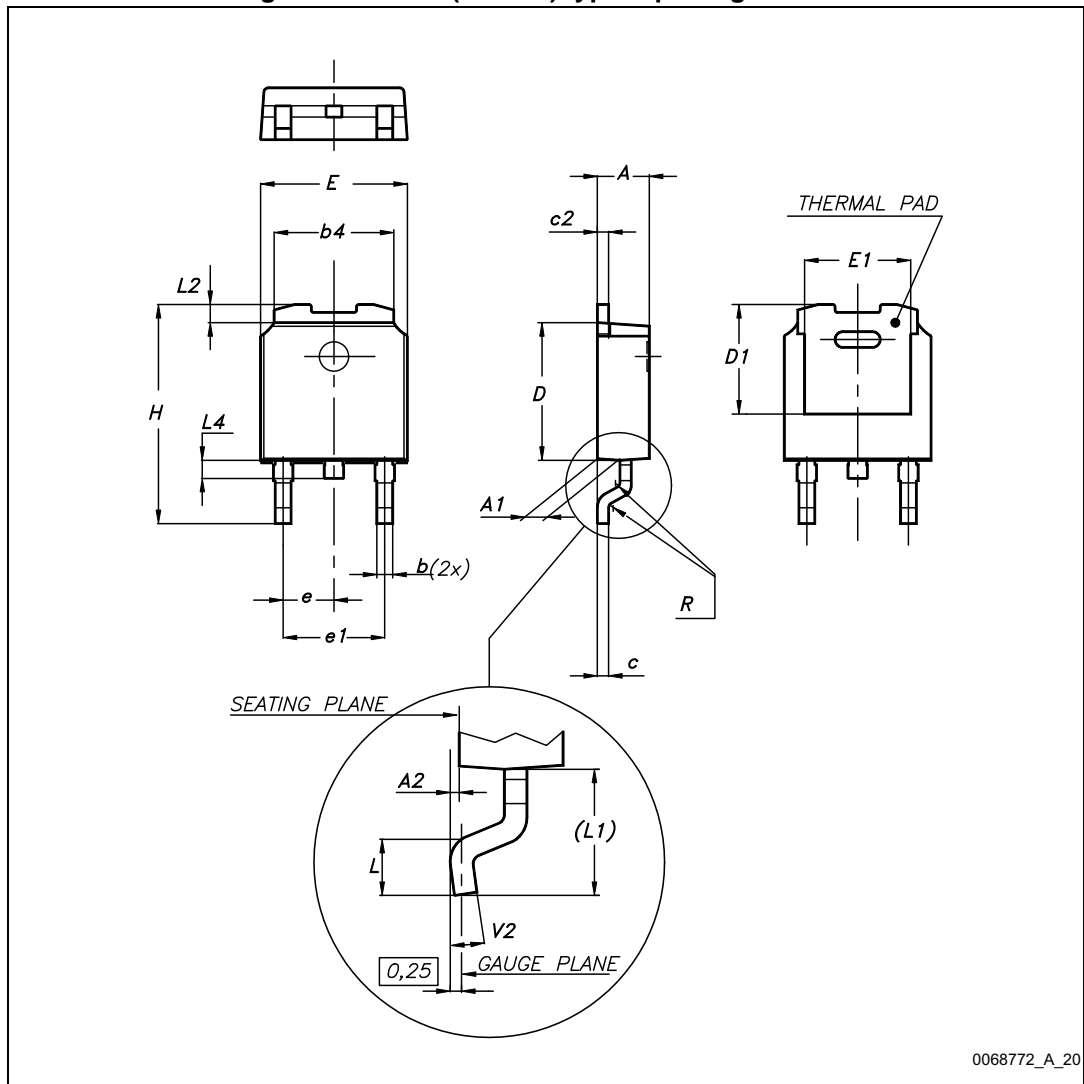


Table 9. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK type E package information

Figure 20. DPAK (TO-252) type E outline

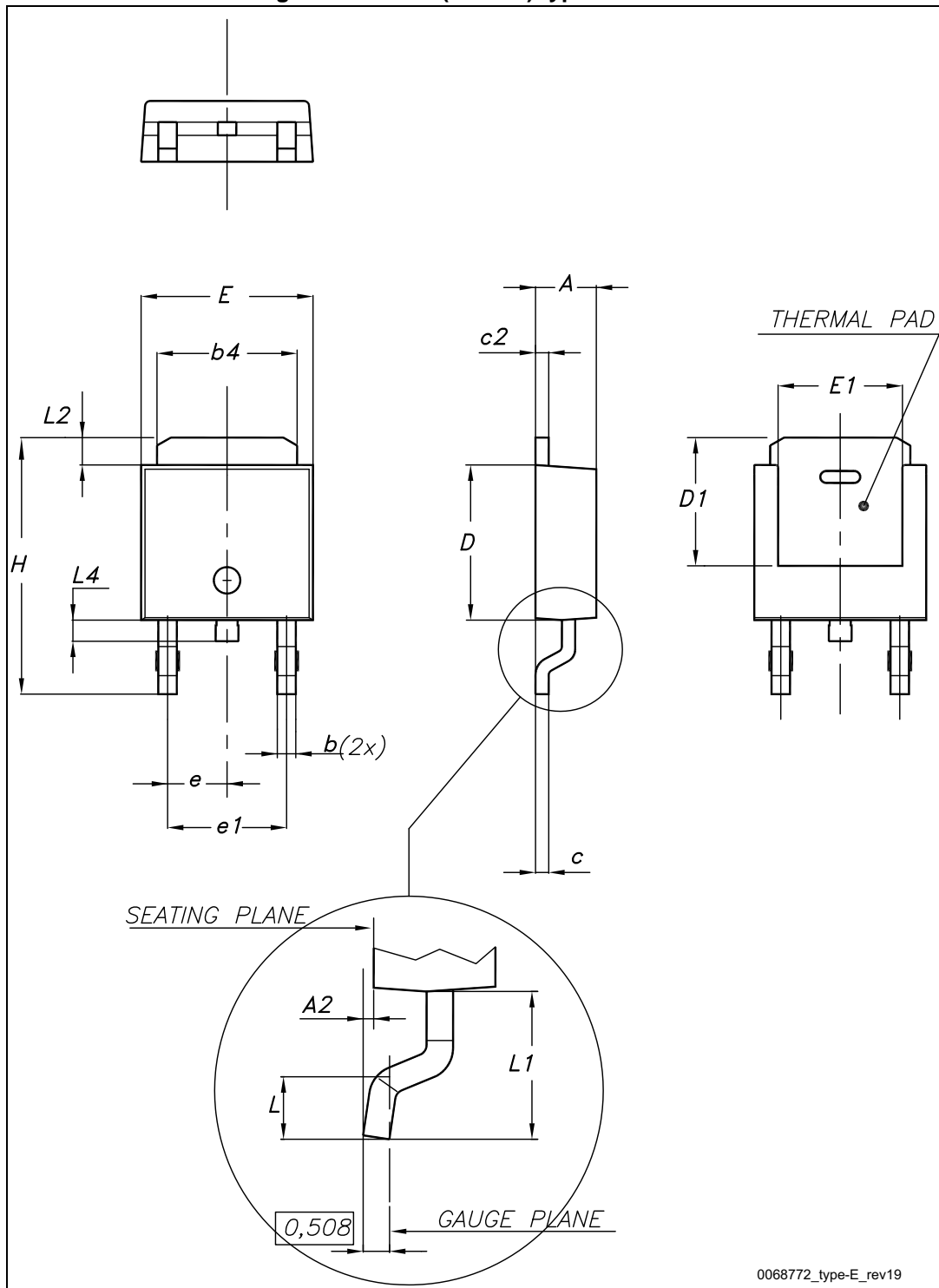
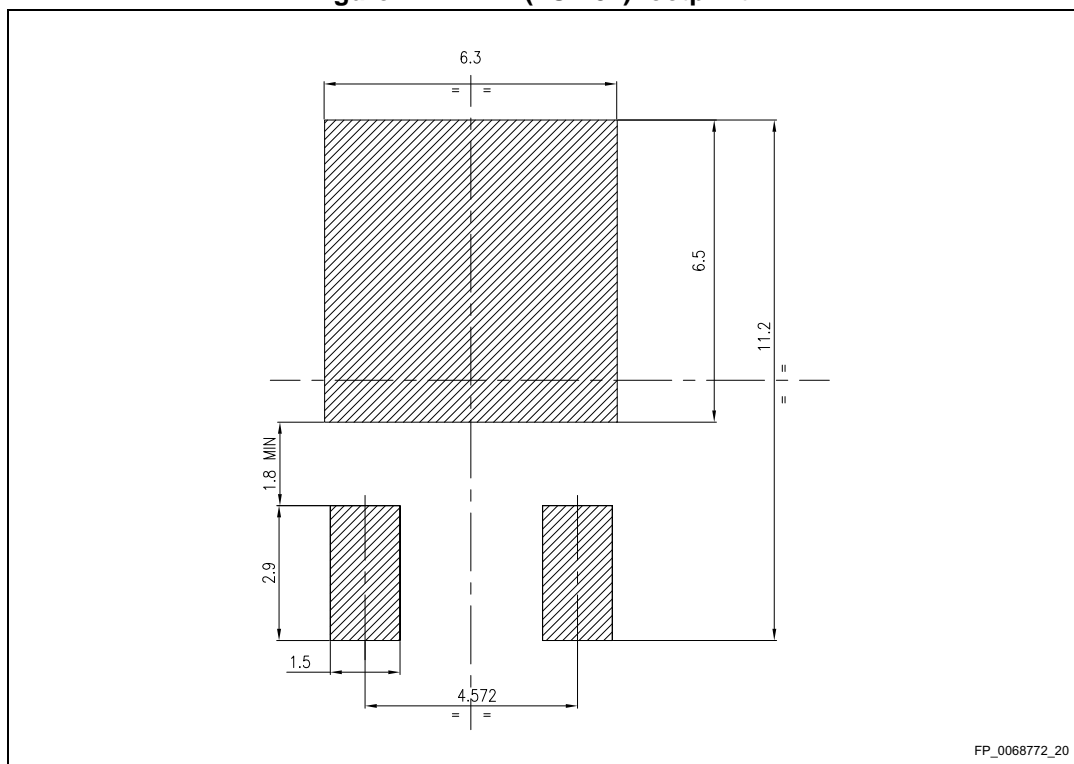


Table 10. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 21. DPAK (TO-252) footprint (a)



a. All dimensions are in millimeters

5 Revision history

Table 11. Document revision history

Date	Revision	Changes
25-Nov-2015	1	First release. Part number previously included in datasheet DocID17156

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